

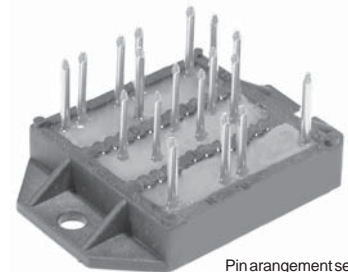
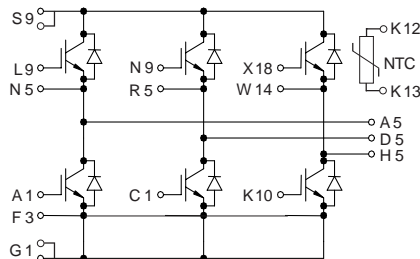
IGBT Module

Sixpack in ECO-PAC 2

VWI 15-12P1

$I_{C25} = 18 \text{ A}$
 $V_{CES} = 1200 \text{ V}$
 $V_{CE(sat)typ.} = 2.3 \text{ V}$

Preliminary data



Pin arrangement see outlines

IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	1200	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	18	A
I_{C80}	$T_C = 80^{\circ}\text{C}$	14	A
I_{CM} V_{CEK}	$V_{GE} = \pm 15 \text{ V}; R_G = 82 \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	20	A
t_{SC} (SCSOA)		$V_{CE} = 720 \text{ V}; V_{GE} = \pm 15 \text{ V}; R_G = 82 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10
P_{tot}	$T_C = 25^{\circ}\text{C}$	90	W

Features

- NPT IGBT's
 - positive temperature coefficient of saturation voltage
 - fast switching
- FRED diodes
 - fast reverse recovery
 - low forward voltage
- Industry Standard Package
 - solderable pins for PCB mounting
 - isolated DCB ceramic base plate

Typical Applications

- AC drives
- power supplies with power factor correction

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 10 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.3	2.7	V
$V_{GE(th)}$	$I_C = 0.4 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.8		0.5 mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			200 nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 10 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 82 \Omega$	50		ns
E_{on}		40		ns
E_{off}		290		ns
		60		ns
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$	600		pF
Q_{Gon}	$V_{CE} = 600 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 10 \text{ A}$	45		nC
R_{thJC}	(per IGBT)		1.4	KW
R_{thJH}	(per IGBT) with heatsink compound	2.7		KW

IXYS reserves the right to change limits, test conditions and dimensions.

© 2003 IXYS All rights reserved

IXYS Semiconductor GmbH
 Edisonstr. 15, D-68623 Lampertheim
 Phone: +49-6206-503-0, Fax: +49-6206-503627

www.ixys.net

IXYS Corporation
 3540 Bassett Street, Santa Clara CA 95054
 Phone: (408) 982-0700, Fax: 408-496-0670

Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	15	A
I_{F80}	$T_C = 80^\circ\text{C}$	10	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 10\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.6	3.0	V
I_{RM} t_{rr}	$I_F = 10\text{ A}; di_F/dt = -400\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 600\text{ V}; V_{GE} = 0\text{ V}$	13		A
		110		ns
R_{thJC}	(per diode)			3.5 K/W
R_{thJH}	(per diode) with heatsink compound	5.0		K/W

Temperature Sensor NTC

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{25}	$T = 25^\circ\text{C}$	4.75	5.0	5.25 k Ω
$B_{25/50}$			3375	K

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-40...+150	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}; t = 1\text{ s}$	3600	V~
M_d	mounting torque (M4)	1.5 - 2.0	Nm
		14 - 18	lb.in.
a	Max. allowable acceleration	50	m/s^2

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_s	Creepage distance on surface (Pin to heatsink)	11.2		mm
d_A	Strike distance in air (Pin to heatsink)	11.2		mm
Weight		24		g

Dimensions in mm (1 mm = 0.0394")
